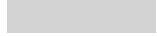




Product Summary

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.



Trench technology

$R_{DS(ON)}$ to minimize conductive loss



nd Synchronous Rectifier



$T_c = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	60	A
	$I_{D@TC=75}$	45	A
	$I_{D@TC=100}$	37	A
Pulsed Drain Current	I_{DM}	180	A
Total Power Dissipation($TC=25$)	$P_D@TC=25$	125	W
Total Power Dissipation($TA=25$)	$P_D@TA=25$	2.5	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@ $L=0.1mH$	E_{AS}	200	mJ



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	1.5	°



Body Diode Reverse Recovery Charge	Qrr			120		
------------------------------------	-----	--	--	-----	--	--

Note:

;

Fig.1 Maximum Safe Operating Area

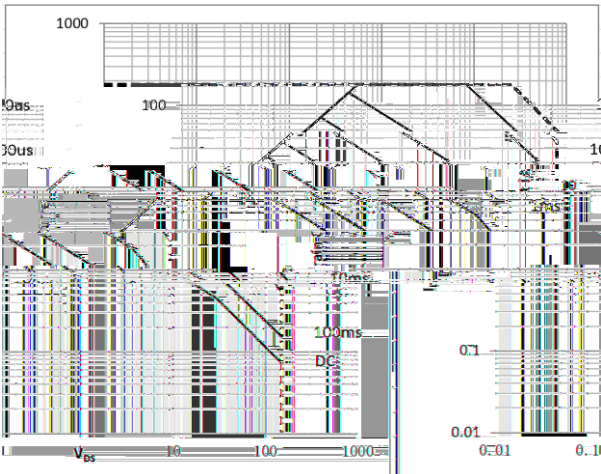


Fig.2 Capacitance Characteristics

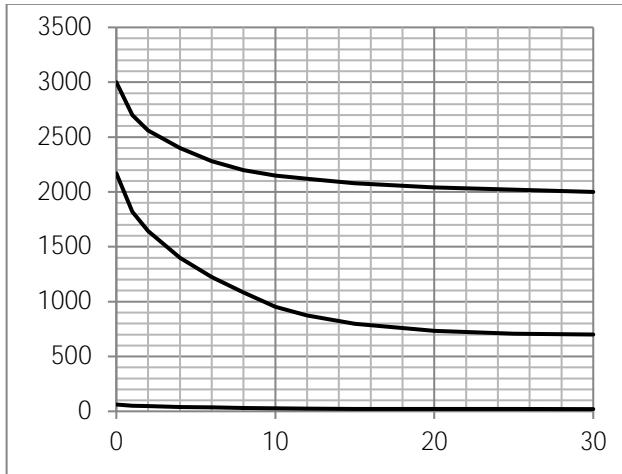


Fig.3 Power Dissipation Derating Curve

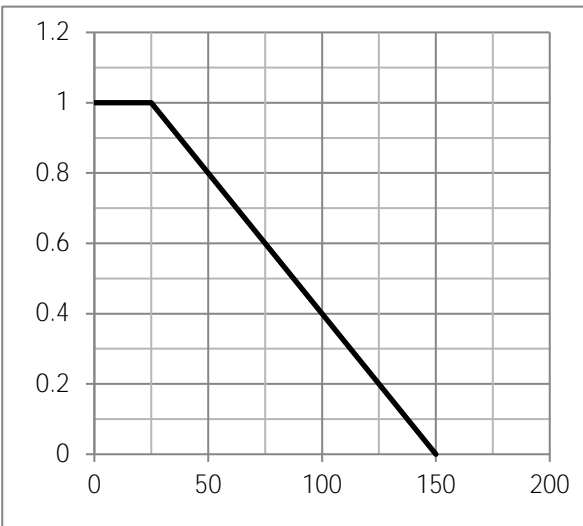


Fig.4 Typical output Characteristics

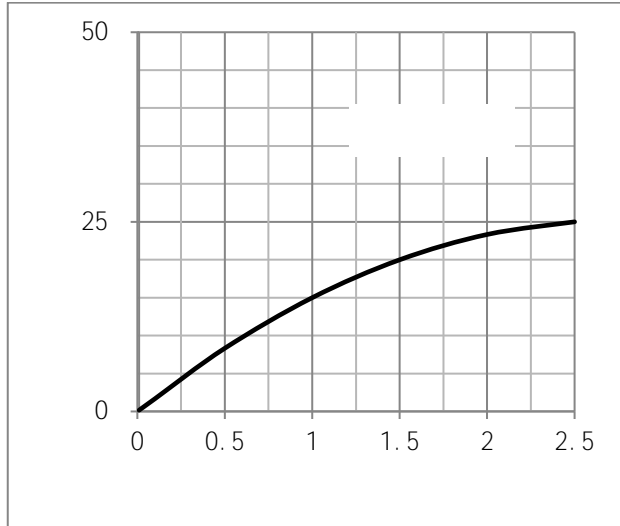




Fig.5 Threshold Voltage V.S Junction Temperature Fig.6 Resistance V.S Drain Current

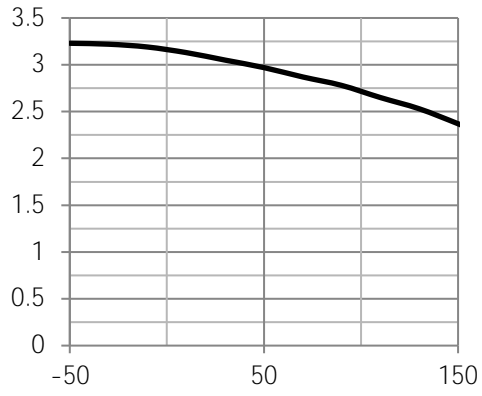


Fig.7 Switching Time Measurement Circuit

Fig.8 Gate Charge Waveform



(TO-220)

Unit mm

	2..		2
	0.		.			0 2	
	..		2.		.		2
	.		..		0 .		2 .
	. 1		.		1..	1 .	2..
	..		.		0 .		1..
	.		.		0..		1..
					1 .		1 .

